OPA5923UYO

Ultra Yellow LED Chip

Ultra Bright

GaAs/AlGaInP

1. Material

Substrate	GaAs	(N Type)
Epitaxial Layer	AlGaInP	(P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

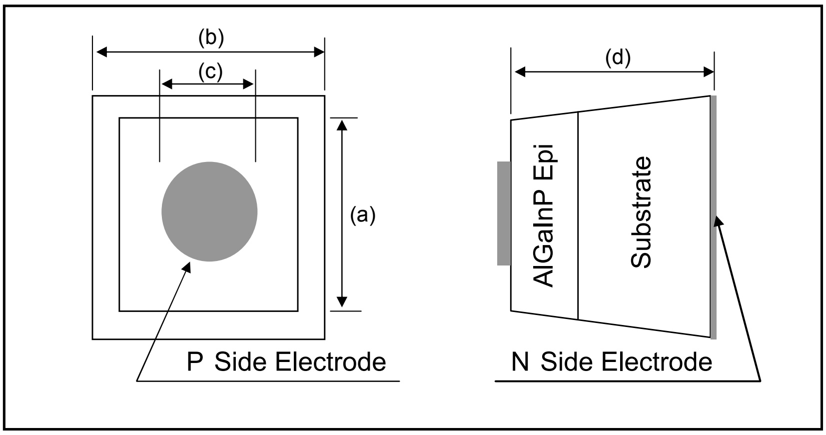
3. Electro-Optical Characteristics

Parameter	Symbol		Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			2.2	2.5	V	IF=20mA
Reverse Curren	I_R				100	uA	VR=5V
Brightness	I_v	A	80	100		mcd	IF=20mA
		B	100	120			
		C	130	140			
		D	140	160			
Wavelength	λ_d			590		nm	IF=20mA
	$\Delta\lambda$			20		nm	IF=20mA

※ Note : Luminous Intensity is measured on bare chips.

4. Mechanical Data

(a) Emission Area -------------------------- 8mil x 8mil
(b) Bottom Area -------------------------- 9mil x 9mil
(c) Bonding Pad -------------------------- 100um
(d) Chip Thickness -------------------------- 7mil



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